

Description

The SX20N06D uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 60V$ $I_D = 28A$

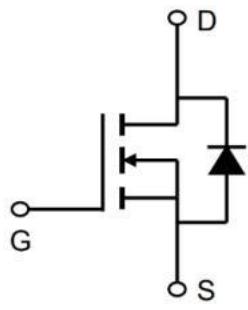
$R_{DS(ON)} < 36m\Omega$ @ $V_{GS}=10V$

Application

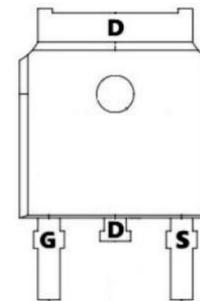
LED lamp

Load switch

Uninterruptible power supply



TO-252-3L

**Absolute Maximum Ratings@ $T_j=25^\circ C$ (unless otherwise specified)**

Symbol	Parameter	Max.	Units
VDSS	Drain-Source Voltage	60	V
VGSS	Gate-Source Voltage	± 20	V
$I_D @ T_c = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	28	A
$I_D @ T_c = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	13	A
IDM	Pulsed Drain Current	74	A
IAS	Avalanche Current	13	A
EAS	Single Pulsed Avalanche Energy	22	mJ
$P_D @ T_c = 25^\circ C$	Power Dissipation	31.3	W
TJ, TSTG	Operating and Storage Temperature Range	-55 to +175	°C
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	62	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	4	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$, $I_D=250\mu\text{A}$	60	65	---	V
$\Delta BVDSS/\Delta T_J$	BVDSS Temperature Coefficient	Reference to 25°C , $I_D=1\text{mA}$	---	0.044	---	$\text{V}/^\circ\text{C}$
RDS(ON)	Static Drain-Source On-Resistance ²	$V_{GS}=10\text{V}$, $I_D=15\text{A}$	---	28	36	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}$, $I_D=7\text{A}$	---	38	45	$\text{m}\Omega$
VGS(th)	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu\text{A}$	1.2	1.6	2.5	V
$\Delta V_{GS(\text{th})}$	$V_{GS(\text{th})}$ Temperature Coefficient		---	-4.8	---	$\text{mV}/^\circ\text{C}$
IDSS	Drain-Source Leakage Current	$V_{DS}=48\text{V}$, $V_{GS}=0\text{V}$, $T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=48\text{V}$, $V_{GS}=0\text{V}$, $T_J=55^\circ\text{C}$	---	---	5	
IGSS	Gate-Source Leakage Current	$V_{GS}=\pm 20\text{V}$, $V_{DS}=0\text{V}$	---	---	± 100	nA
gfs	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=15\text{A}$	---	25.3	---	S
R _g	Gate Resistance	$V_{DS}=0\text{V}$, $V_{GS}=0\text{V}$, $f=1\text{MHz}$	---	2.5	---	Ω
Q _g	Total Gate Charge (10V)	$V_{DS}=48\text{V}$, $V_{GS}=10\text{V}$, $I_D=15\text{A}$	---	19	---	nC
Q _{gs}	Gate-Source Charge		---	2.5	---	
Q _{gd}	Gate-Drain Charge		---	5	---	
Td(on)	Turn-On Delay Time	$V_{DD}=30\text{V}$, $V_{GS}=10\text{V}$, $R_G=3.3\Omega$ $I_D=15\text{A}$	---	2.8	---	ns
T _r	Rise Time		---	16.6	---	
Td(off)	Turn-Off Delay Time		---	21.2	---	
T _f	Fall Time		---	5.6	---	
C _{iss}	Input Capacitance	$V_{DS}=15\text{V}$, $V_{GS}=0\text{V}$, $f=1\text{MHz}$	---	1027	---	pF
C _{oss}	Output Capacitance		---	65	---	
C _{rss}	Reverse Transfer Capacitance		---	46	---	
I _s	Continuous Source Current ^{1,6}	$V_G=V_D=0\text{V}$, Force Current	---	---	20	A
ISM	Pulsed Source Current ^{2,6}		---	---	40	A
VSD	Diode Forward Voltage ²	$V_{GS}=0\text{V}$, $I_S=1\text{A}$, $T_J=25^\circ\text{C}$	---	---	1.2	V
t _{rr}	Reverse Recovery Time	IF=15A, $dI/dt=100\text{A}/\mu\text{s}$, $T_J=25^\circ\text{C}$	---	12.2	---	nS
Q _{rr}	Reverse Recovery Charge		---	7.3	---	nC

Note :

- 1、The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width .The EAS data shows Max. rating .
- 3、The test cond $\leq 300\mu\text{s}$ duty cycle $\leq 2\%$, duty cycle ition is $T_J =25^\circ\text{C}$, $VDD =48\text{V}$, $VG =10\text{V}$, $RG =25\Omega$, $L=0.1\text{mH}$, $IAS =13\text{A}$
- 4、The power dissipation is limited by 175°C junction temperature
- 5、The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Typical Characteristics

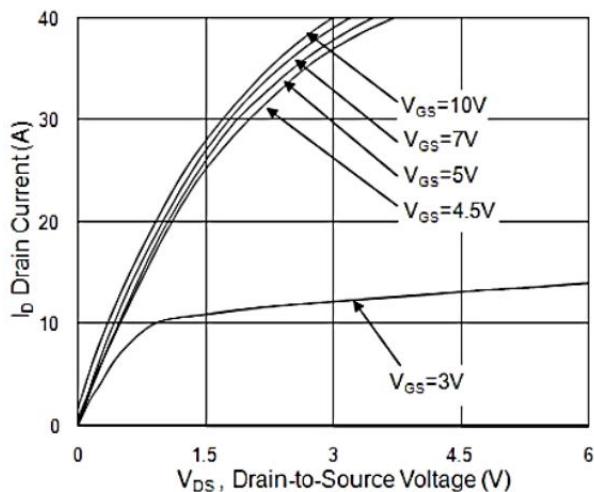


Fig.1 Typical Output Characteristics

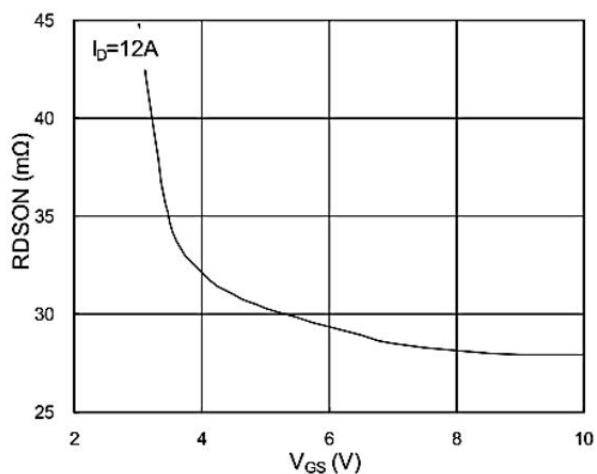


Fig.2 On-Resistance vs. Gate-Source

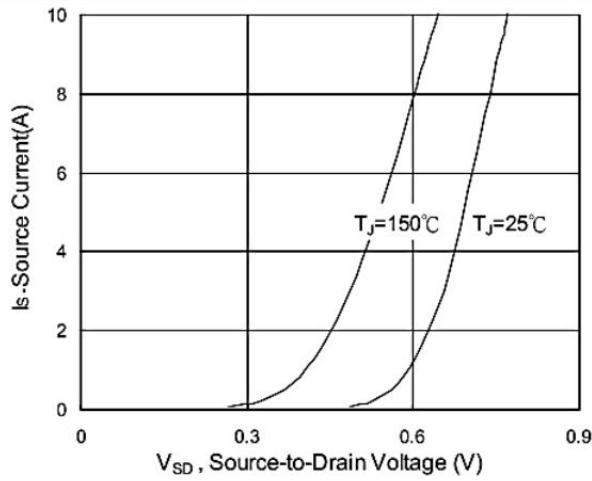


Fig.3 Forward Characteristics Of Reverse

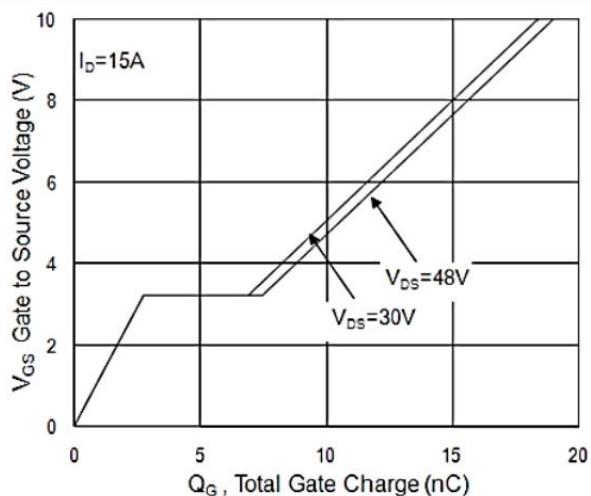


Fig.4 Gate-Charge Characteristics

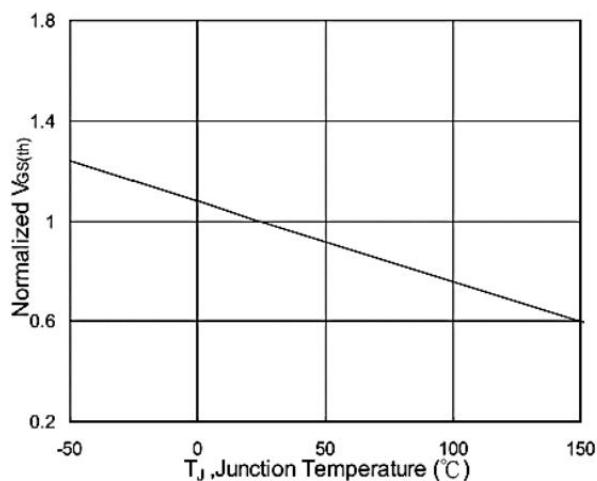


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

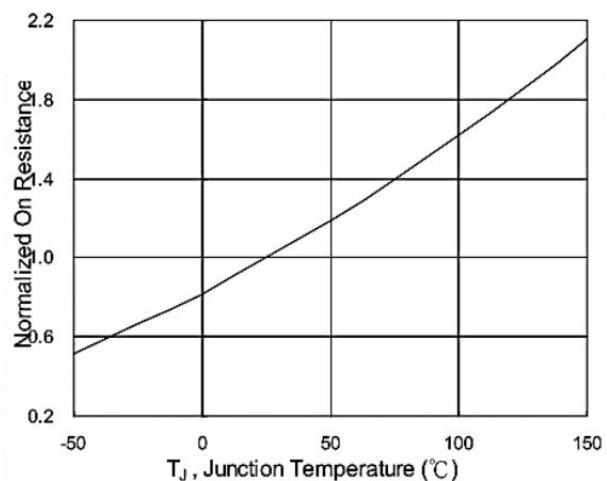


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

Typical Characteristics

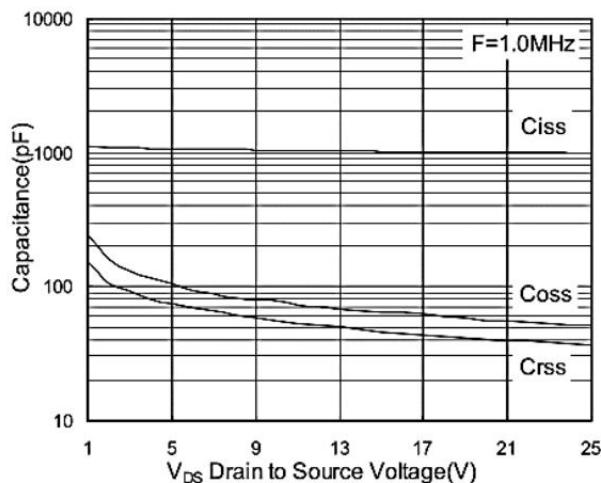


Fig.7 Capacitance

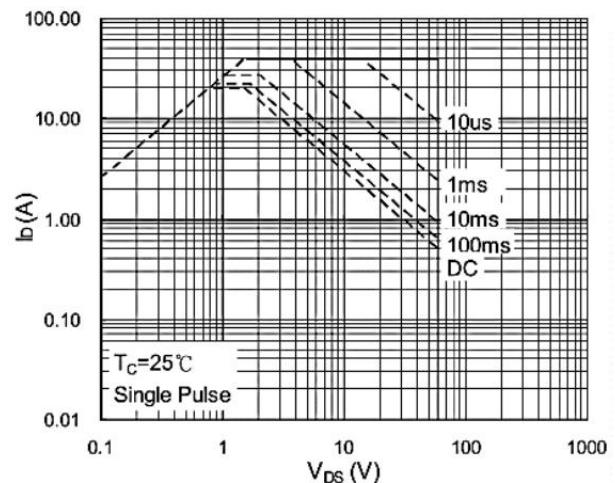


Fig.8 Safe Operating Area

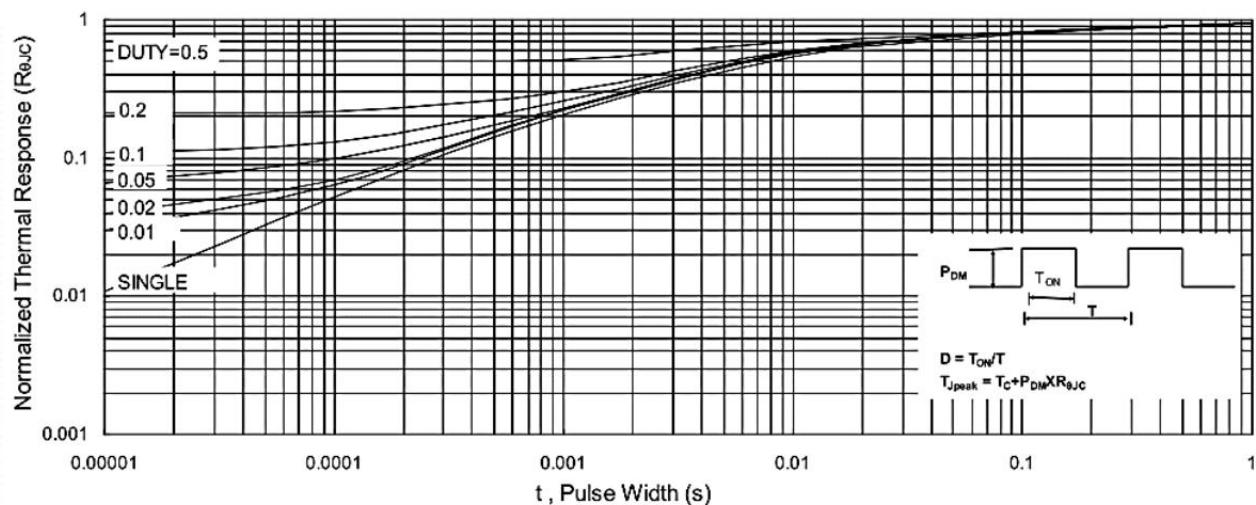


Fig.9 Normalized Maximum Transient Thermal Impedance

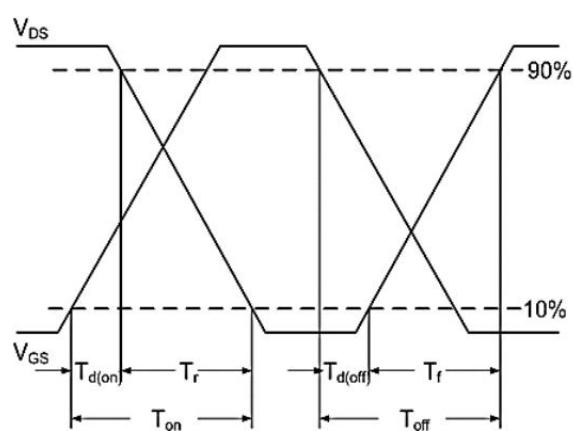


Fig.10 Switching Time Waveform

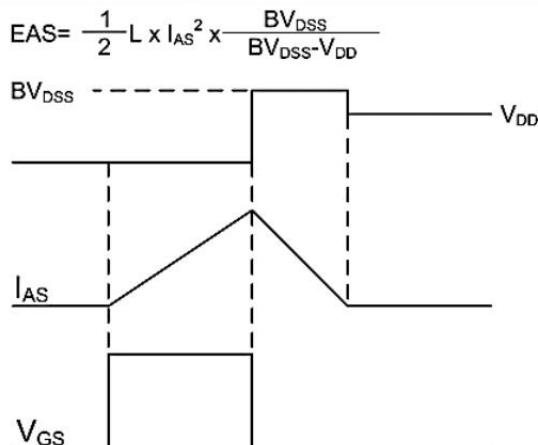
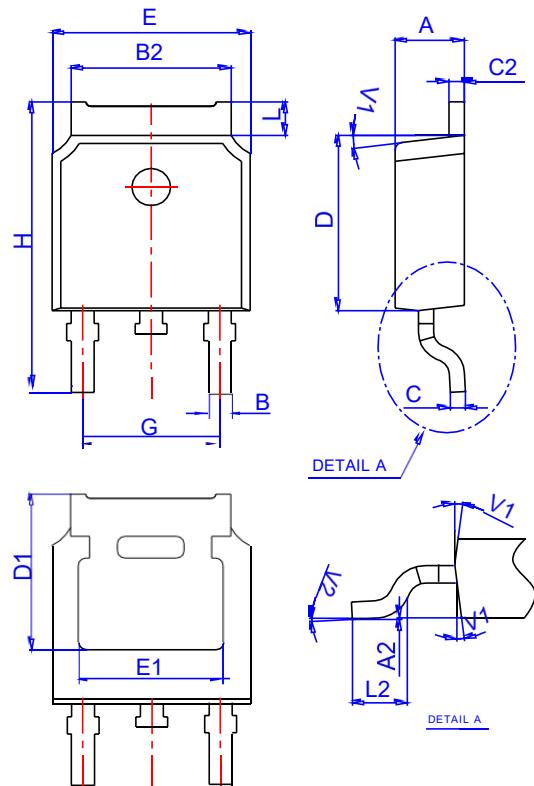


Fig.11 Unclamped Inductive Switching Waveform

Package Mechanical Data: TO-252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	TO-252-3L		2500